

## 1.Description

This P-Channel 2.5V specified MOSFET has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for portable electronics applications: load switching and power management, battery charging circuits and DC/DC conversion.

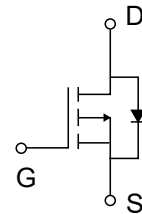
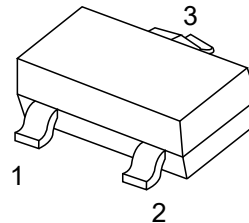
## 2.Features

- $V_{DS(V)} = -20V$
- $R_{DS(ON)} < 0.14\Omega (V_{GS} = -4.5V)$
- $R_{DS(ON)} < 0.16\Omega (V_{GS} = -2.5V)$

## 3.Pinning information

| Pin | Symbol | Description |
|-----|--------|-------------|
| 1   | G      | GATE        |
| 2   | S      | SOURCE      |
| 3   | D      | DRAIN       |

### SOT-23



## 4.Maximum ratings ( $T_A = 25^\circ C$ unless otherwise noted)

| Parameter                                         | Symbol          | Value      | Units        |
|---------------------------------------------------|-----------------|------------|--------------|
| Drain-Source Voltage                              | $V_{DSS}$       | -20        | V            |
| Gate-Source Voltage                               | $V_{GSS}$       | $\pm 8$    | V            |
| Drain Current – Continuous (Note 1a)              | $I_D$           | -1.3       | A            |
| – Pulsed                                          |                 | -10        |              |
| Maximum Power Dissipation (Note 1a)               | $P_D$           | 0.5        | W            |
| (Note 1b)                                         |                 | 0.46       |              |
| Operating and Storage Junction Temperature Range  | $T_J, T_{STG}$  | -55 to 150 | $^\circ C$   |
| <b>Thermal Characteristics</b>                    |                 |            |              |
| Thermal Resistance, Junction-to-Ambient (Note 1a) | $R_{\theta JA}$ | 250        | $^\circ C/W$ |
| Thermal Resistance, Junction-to-Case (Note 1)     | $R_{\theta JC}$ | 75         | $^\circ C/W$ |



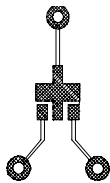
## 5. Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter                                | Symbol                       | Conditions                                                 | Min  | Typ   | Max  | Units    |
|------------------------------------------|------------------------------|------------------------------------------------------------|------|-------|------|----------|
| OFF CHARACTERISTICS                      |                              |                                                            |      |       |      |          |
| Drain-source breakdown voltage           | $BV_{DSS}$                   | $V_{GS}=0V, I_D=-250\mu A$                                 | -20  |       |      | V        |
| Breakdown Voltage Temp. Coefficient      | $\Delta BV_{DSS}/\Delta T_J$ | $I_D=-250\mu A$<br>Referenced to 25°C                      |      | -16   |      | mV/°C    |
| Zero Gate Voltage Drain Current          | $I_{DSS}$                    | $V_{DS}=-16V, V_{GS}=0V$                                   |      |       | -1   | $\mu A$  |
|                                          |                              | $T_J=55^\circ C$                                           |      |       | -10  | $\mu A$  |
| Gate - Body Leakage, Forward             | $I_{GSSF}$                   | $V_{GS}=8V, V_{DS}=0V$                                     |      |       | 100  | nA       |
| Gate - Body Leakage, Reverse             | $I_{GSSR}$                   | $V_{GS}=-8V, V_{DS}=0V$                                    |      |       | -100 | nA       |
| ON CHARACTERISTICS (Note)                |                              |                                                            |      |       |      |          |
| Gate Threshold Voltage                   | $V_{GS(th)}$                 | $V_{DS}=V_{GS}, I_D=-250\mu A$                             | -0.4 | -0.9  | -1.5 | V        |
| Gate Threshold Voltage Temp. Coefficient | $\Delta V_{GS(th)}/T_J$      | $I_D=-250\mu A$<br>Referenced to 25°C                      |      | 3     |      | mV/°C    |
| Static Drain-Source On-Resistance        | $R_{DS(ON)}$                 | $V_{GS}=-4.5V, I_D=-1.3A$                                  |      | 0.084 | 0.14 | $\Omega$ |
|                                          |                              | $T_J=25^\circ C$                                           |      | 0.18  | 0.32 |          |
|                                          |                              | $V_{GS}=-2.5V, I_D=-1.1A$                                  |      | 0.11  | 0.16 |          |
| On-State Drain Current                   | $I_{D(ON)}$                  | $V_{GS}=-4.5V, V_{DS}=-5V$                                 | -5   |       |      | A        |
| Forward Transconductance                 | $g_{FS}$                     | $V_{DS}=-4.5V, I_D=-2A$                                    |      | 4     |      | S        |
| DYNAMIC CHARACTERISTICS                  |                              |                                                            |      |       |      |          |
| Input Capacitance                        | $C_{iss}$                    | $V_{GS}=0V, V_{DS}=-10V, f=1MHz$                           |      | 330   |      | pF       |
| Output Capacitance                       | $C_{oss}$                    |                                                            |      | 80    |      | pF       |
| Reverse Transfer Capacitance             | $C_{rss}$                    |                                                            |      | 35    |      | pF       |
| SWITCHING CHARACTERISTICS (Note)         |                              |                                                            |      |       |      |          |
| Turn - On Delay Time                     | $t_{D(on)}$                  | $V_{DD}=-5V, I_D=-0.5A$<br>$V_{GS}=-4.5V, R_{GEN}=6\Omega$ |      | 7     | 15   | ns       |
| Turn - On Rise Time                      | $t_r$                        |                                                            |      | 12    | 22   | ns       |
| Turn - Off Delay Time                    | $t_{D(off)}$                 |                                                            |      | 16    | 26   | ns       |
| Turn - Off Fall Time                     | $t_f$                        |                                                            |      | 5     | 12   | ns       |

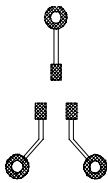


|                                                        |                 |                                                    |  |      |       |    |
|--------------------------------------------------------|-----------------|----------------------------------------------------|--|------|-------|----|
| Total Gate Charge                                      | Q <sub>g</sub>  | V <sub>DS</sub> =-10V, I <sub>D</sub> =-2A         |  | 3.6  | 5     | nC |
| Gate-Source Charge                                     | Q <sub>gs</sub> |                                                    |  | 0.8  |       | nC |
| Gate-Drain Charge                                      | Q <sub>gd</sub> | V <sub>GS</sub> =-4.5V                             |  | 0.7  |       | nC |
| Drain–Source Diode Characteristics and Maximum Ratings |                 |                                                    |  |      |       |    |
| Maximum Continuous Drain–Source Diode Forward Current  | I <sub>s</sub>  |                                                    |  |      | -0.42 | A  |
|                                                        |                 |                                                    |  |      |       |    |
| Drain–Source Diode Forward Voltage                     | V <sub>SD</sub> | V <sub>GS</sub> =0V, I <sub>s</sub> =-0.42A (Note) |  | -0.7 | -1.2  | V  |

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a. 250°C/W when mounted on  
a 0.02 in<sup>2</sup> pad of 2oz Cu.



b) 270°C/W when mounted on a  
0.001 in<sup>2</sup> pad of 2oz Cu.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%



## 6.1 Typical Characteristics

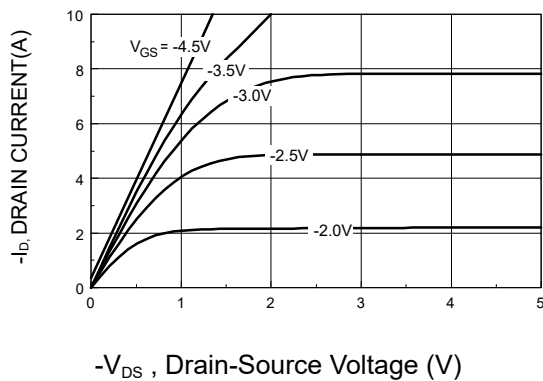


Figure 1: On-Region Characteristics.

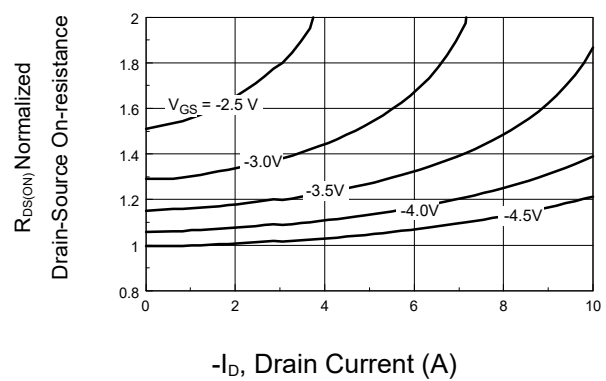


Figure 2: On-Resistance Variation with Drain Current and Gate Voltage.

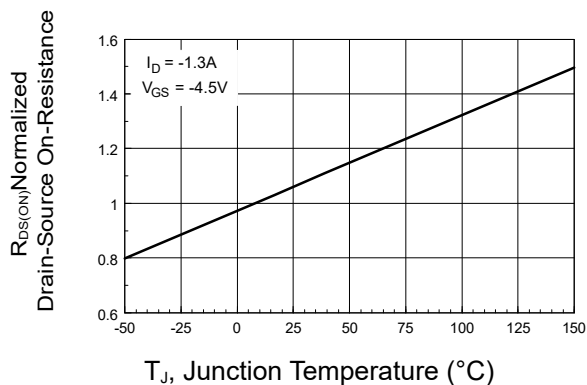


Figure 3: On-Resistance Variation with Temperature.

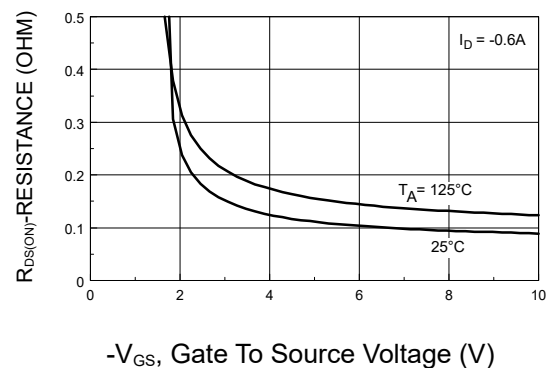


Figure 4: On-Resistance Variation with Gate-to-Source Voltage.

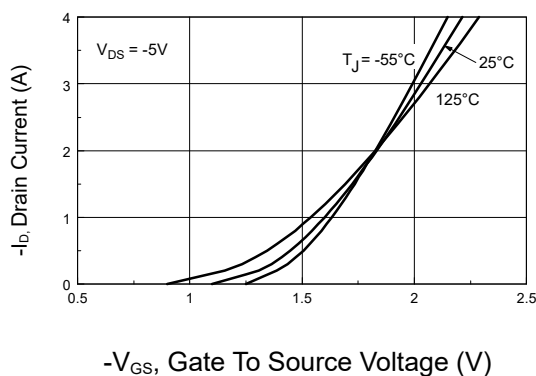


Figure 5: Transfer Characteristics.

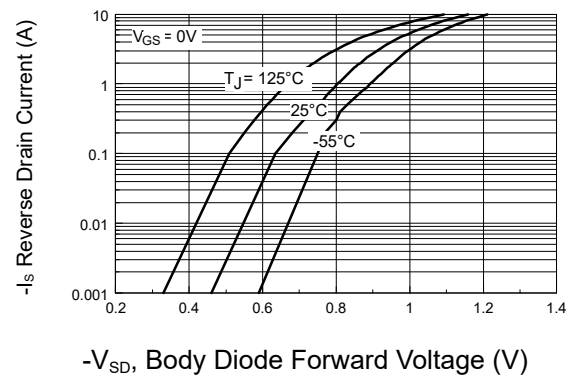


Figure 6: . Body Diode Forward Voltage Variation with Source Current and Temperature.



## 6.2 Typical Characteristics

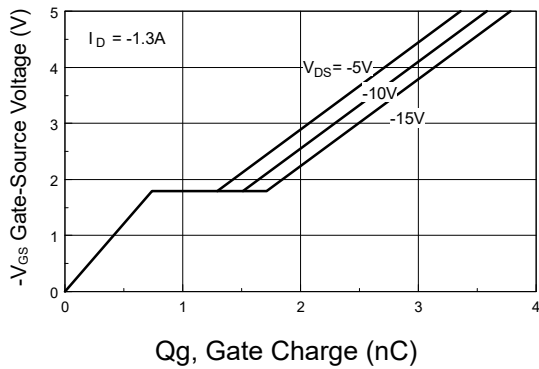


Figure 7: Gate-Charge Characteristics

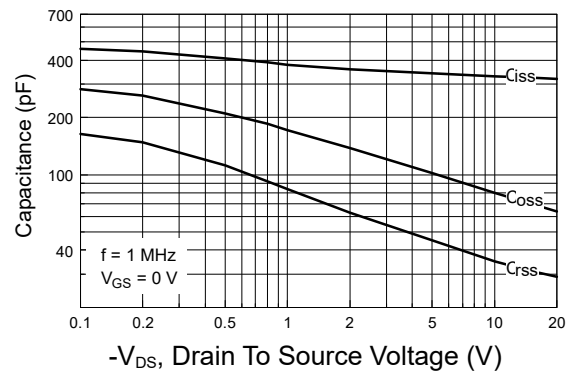


Figure 8: Capacitance Characteristics

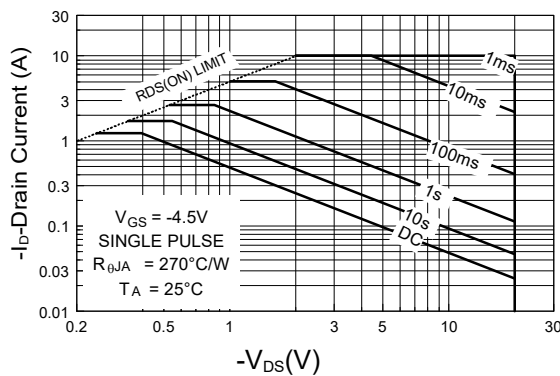


Figure 9: Maximum Safe Operating Area.

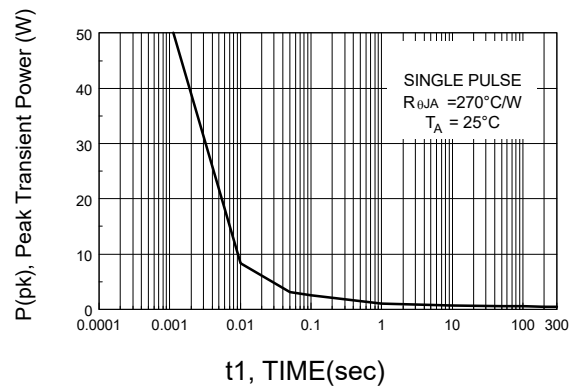


Figure 10: Single Pulse Maximum Power Dissipation.

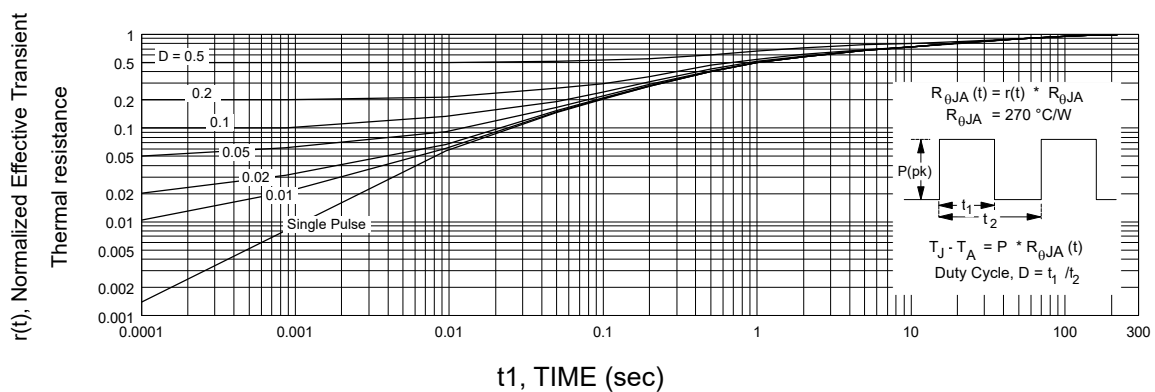
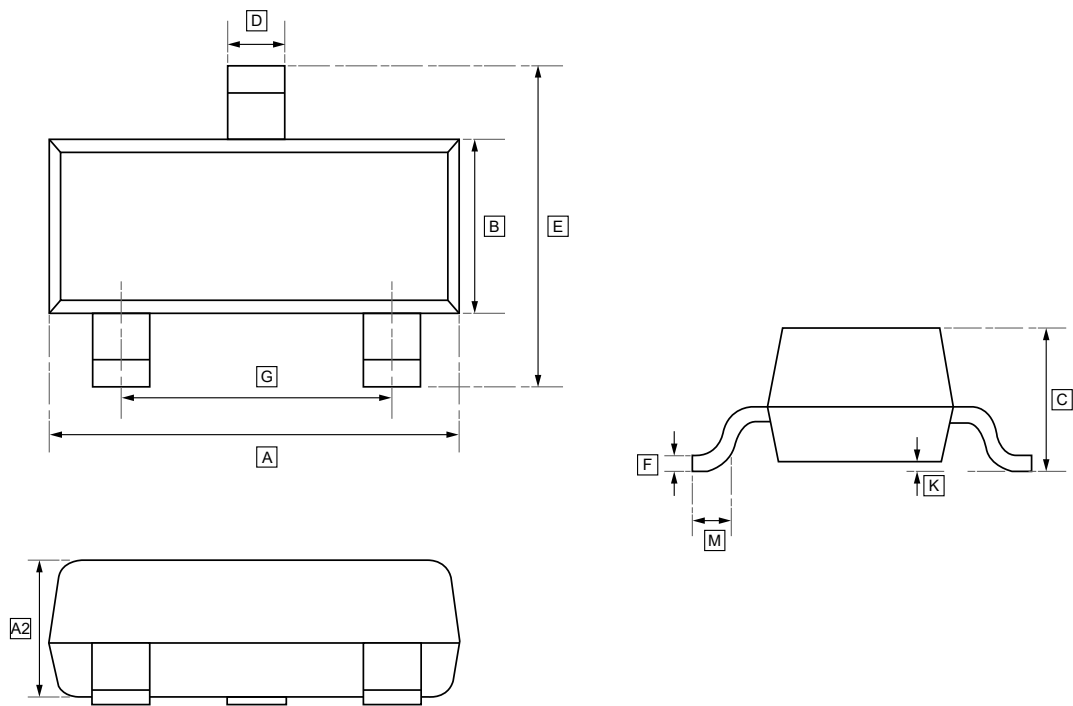


Figure 11. Transient Thermal Response Curve.



7.SOT-23 Package Outline Dimensions

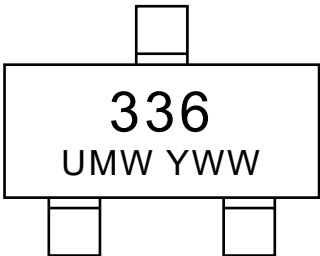


DIMENSIONS (mm are the original dimensions)

| Symbol | A    | B    | C    | D    | E    | G    | K    | M    | A2   | F     |
|--------|------|------|------|------|------|------|------|------|------|-------|
| Min    | 2.85 | 1.20 | 0.90 | 0.40 | 2.25 | 1.80 | 0.00 | 0.30 | 0.95 | 0.095 |
| Max    | 3.04 | 1.40 | 1.10 | 0.50 | 2.55 | 2.00 | 0.10 | -    | 1.05 | 0.115 |



8.Ordering information



| Order Code  | Package | Base QTY | Delivery Mode |
|-------------|---------|----------|---------------|
| UMW FDN336P | SOT-23  | 3000     | Tape and reel |



## 9.Disclaimer

UMW reserves the right to make changes to all products, specifications. Customers should obtain the latest version of product documentation and verify the completeness and currency of the information before placing an order.

When applying our products, please do not exceed the maximum rated values, as this may affect the reliability of the entire system. Under certain conditions, any semiconductor product may experience faults or failures. Buyers are responsible for adhering to safety standards and implementing safety measures during system design, prototyping, and manufacturing when using our products to prevent potential failure risks that could lead to personal injury or property damage.

Unless explicitly stated in writing, UMW products are not intended for use in medical, life-saving, or life-sustaining applications, nor for any other applications where product failure could result in personal injury or death. If customers use or sell the product for such applications without explicit authorization, they assume all associated risks.

When reselling, applying, or exporting, please comply with export control laws and regulations of China, the United States, the United Kingdom, the European Union, and other relevant countries, regions, and international organizations.

This document and any actions by UMW do not grant any intellectual property rights, whether express or implied, by estoppel or otherwise. The product names and marks mentioned herein may be trademarks of their respective owners.